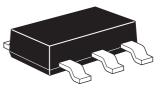


# ZXMS6001N3 60V N-channel self protected enhancement mode *INTELLIFET*™ MOSFET

### Summary

Continuous drain source voltage $V_{DS} = 60V$ On-state resistance $675m\Omega$ Max nominal load current (a) $1.1A (V_{IN} = 5V)$ Min nominal load current (c) $0.7A (V_{IN} = 5V)$ Clamping Energy550mJ



## Description

Low input current self protected low side MOSFET intended for Vin=5V applications. Monolithic over temperature, over current, over voltage (active clamp) and ESD protected logic level functionality. Intended as a general purpose switch.

### Note:

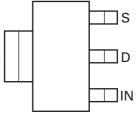
The tab is connected to the source pin and must be electrically isolated from the drain pin. Connection of significant copper to the drain pin is recommended for best thermal performance.

### Features

- · Short circuit protection with auto restart
- Over voltage protection (active clamp)
- Thermal shutdown with auto restart
- Over-current protection
- Input protection (ESD)
- · Load dump protection (actively protects load)
- · Low input current

## Ordering information

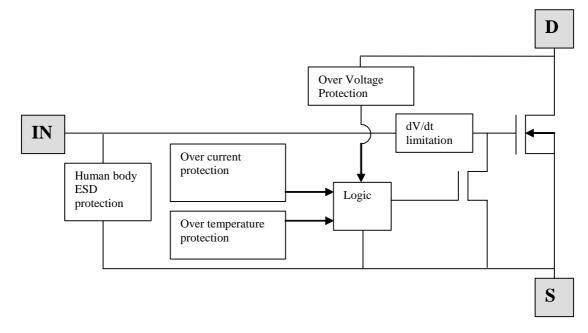
Device	Package	Part mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6001N3TA	SOT223	ZXMS6001	7	12 embossed	1,000



S



## Functional block diagram



## **Applications and information**

- Especially suited for loads with a high in-rush current such as lamps and motors.
- All types of resistive, inductive and capacitive loads in switching applications.
- $\mu$ C compatible power switch for 12V and 24V DC applications.
- Automotive rated.
- Replaces electromechanical relays and discrete circuits.

Linear Mode capability - the current-limiting protection circuitry is designed to de-activate at low Vds, in order not to compromise the load current during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the products ability to self protect itself at low  $V_{DS}$ .

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Continuous Drain-Source Voltage	V <sub>DS</sub>	60	V
Drain-Source Voltage for short circuit protection $V_{IN} = 5V$	V <sub>DS(SC)</sub>	36	V
Continuous Input Voltage	V <sub>IN</sub>	-0.2 +10	V
Peak Input Voltage	V <sub>IN</sub>	-0.2 +20	V
Continuous Input Current -0.2V=V <sub>IN</sub> =10V V <sub>IN</sub> <-0.2V or V <sub>IN</sub> >10V	I <sub>IN</sub>	No limit ∣ I <sub>IN</sub>  ≤2	mA
Operating Temperature Range	T <sub>j</sub> ,	-40 to +150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Power Dissipation at $T_A = 25^{\circ}C^{(a)}$	PD	1.5	W
Power Dissipation at $T_A = 25^{\circ}C^{(c)}$	PD	0.6	W
Continuous Drain Current @ V <sub>IN</sub> =5V; T <sub>A</sub> =25°C <sup>(a)</sup>	۱ <sub>D</sub>	1.1	А
Continuous Drain Current @ V <sub>IN</sub> =5V; T <sub>A</sub> =25°C <sup>(c)</sup>	۱ <sub>D</sub>	0.7	А
Continuous Source Current (Body Diode) <sup>(a)</sup>	۱ <sub>S</sub>	2.0	А
Pulsed Source Current (Body Diode) <sup>(b)</sup>	۱ <sub>S</sub>	3.3	А
Unclamped single pulse inductive energy	E <sub>AS</sub>	550	mJ
Load dump protection	V <sub>LoadDump</sub>	80	V
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		40/150/56	

### **Thermal resistance**

Parameter	Symbol	Value	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	83	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	45	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	208	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 board with a high coverage of single sided 2oz weight copper. Allocation of 6cm<sup>2</sup> copper 33% to source tab and 66% to drain pin with source tab and drain pin electrically isolated.

(b) For a device surface mounted on FR4 board as (a) and measured at t<=10s.

(c) For a device surface mounted on FR4 board with the minimum copper required for electrical connections.

## **Recommended operating conditions**

The ZXMS6001 is optimized for use with  $\mu$ C operating from 5V supplies.

Symbol	Description	Min	Max	Units
V <sub>IN</sub>	Input voltage range	0	6	V
T <sub>A</sub>	Ambient temperature range	-40	125	°C
V <sub>IH</sub>	High level input voltage for MOSFET <sup>(d)</sup>	4	6	V
V <sub>P</sub>	Peripheral supply voltage (voltage to which load is referred)		60	V

## Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Static Characteristics			1		1	
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	70	75	V	I <sub>D</sub> =10mA
Off state Drain Current	I <sub>DSS</sub>		0.1	3	μA	V <sub>DS</sub> =12V, V <sub>IN</sub> =0V
Off state Drain Current	I <sub>DSS</sub>		3	15	μA	V <sub>DS</sub> =32V, V <sub>IN</sub> =0V
Input Threshold Voltage <sup>(d)</sup>	V <sub>IN(th)</sub>	1	1.8	2.5	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =10mA
Input Current	I <sub>IN</sub>		150		μA	V <sub>IN</sub> =+3V
Input Current	I <sub>IN</sub>		335	500	μΑ	V <sub>IN</sub> =+5V, all circumstances
Static Drain-Source On-State Resistance	R <sub>DS(on)</sub>		1	2	Ω	V <sub>IN</sub> =3V, I <sub>D</sub> =0.1A
Static Drain-Source On-State Resistance	R <sub>DS(on)</sub>		520	675	mΩ	V <sub>IN</sub> =5V, I <sub>D</sub> =0.7A
Current Limit <sup>(e)</sup>	I <sub>D(LIM)</sub>	1	1.8	3	А	V <sub>IN</sub> =5V, V <sub>DS</sub> >5V
Dynamic Characteristics						
Turn-On Time (V <sub>IN</sub> to 90% I <sub>D</sub> )	t <sub>on</sub>		27	40	μS	R <sub>L</sub> =22Ω, V <sub>IN</sub> =0 to 5V, V <sub>DD</sub> =12V
Turn-Off time (V <sub>IN</sub> to 90% I <sub>D</sub> )	t <sub>off</sub>		26	40	μS	$R_L=22\Omega$ , $V_{IN}=5V$ to 0V, $V_{DD}=12V$
Slew Rate On (70 to 50% V <sub>DD</sub> )	-dV <sub>DS</sub> /dt <sub>on</sub>		1.4	10	V/µs	$R_L=22\Omega$ , $V_{IN}=0$ to 5V, $V_{DD}=12V$
Slew Rate Off (50 to 70% V <sub>DD</sub> )	DV <sub>DS</sub> /dt <sub>on</sub>		1.2	10	V/µs	$R_L=22\Omega$ , $V_{IN}=5V$ to 0V, $V_{DD}=12V$

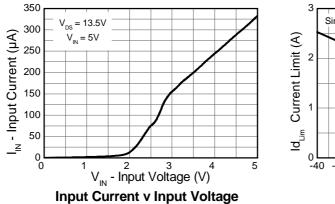
### NOTES:

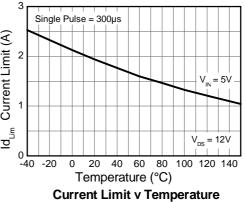
(d) Recommended input voltage range over which protection circuits function as specified.

(e) The drain current is limited to a reduced value when Vds exceeds a safe level

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Protection Functions (f)						
Minimum input voltage for over temperature protection	V <sub>PROT</sub>	4	3.5		V	Ttrip>150°C
Maximum input voltage for over temperature protection	V <sub>PROT</sub>		7	6	V	Ttrip>150°C
Thermal Overload Trip Temperature	T <sub>JT</sub>	150	175		°C	
Thermal hysteresis			8		°C	
Unclamped single pulse inductive energy Tj=25°C	E <sub>AS</sub>	550			mJ	I <sub>D(ISO)</sub> =0.7A, V <sub>DD</sub> =32V
Unclamped single pulse inductive energy Tj=150°C	E <sub>AS</sub>	200			mJ	I <sub>D(ISO)</sub> =0.7A, V <sub>DD</sub> =32V
Inverse Diode						
Source drain voltage	V <sub>SD</sub>			1	V	V <sub>IN</sub> =0V, -I <sub>D</sub> =1.4A

f Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.





## **Application information**

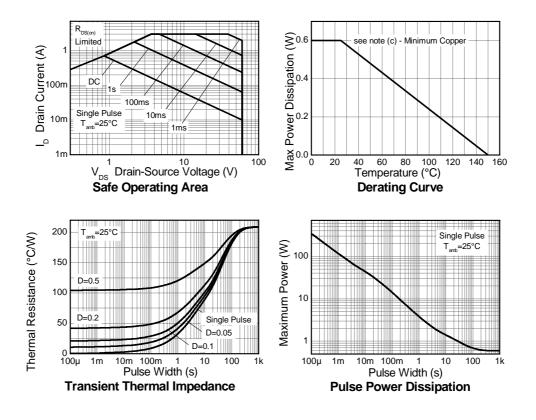
The current-limit protection circuitry is designed to de-activate at low Vds to prevent the load current from being unnecessarily restricted during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry (see graph page 8 'typical output characteristic'). This does not compromise the products ability to self protect at low V<sub>DS</sub>.

The overtemperature protection circuit trips at a minimum of 150°C. So the available package dissipation reduces as the maximum required ambient temperature increases. This leads to the following maximum recommended continuous operating currents.

### Minimum copper area characteristics

For minimum copper condition as described in note (c)

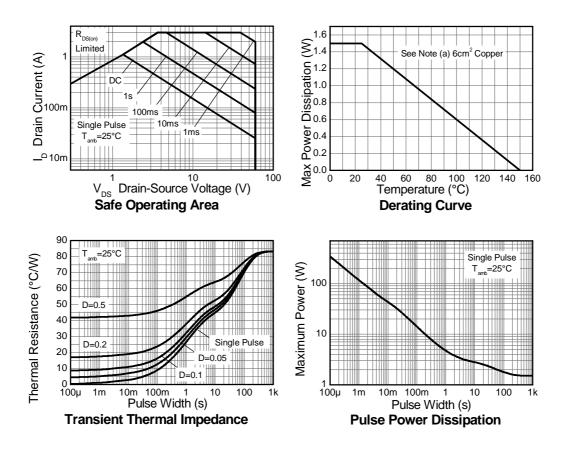
Max Ambient Temperature T <sub>A</sub>	Maximum continuous current V <sub>IN</sub> =5V
25°C at Vin=5V	720
70°C at Vin=5V	575
85°C at Vin=5V	520
125°C at Vin=5V	320

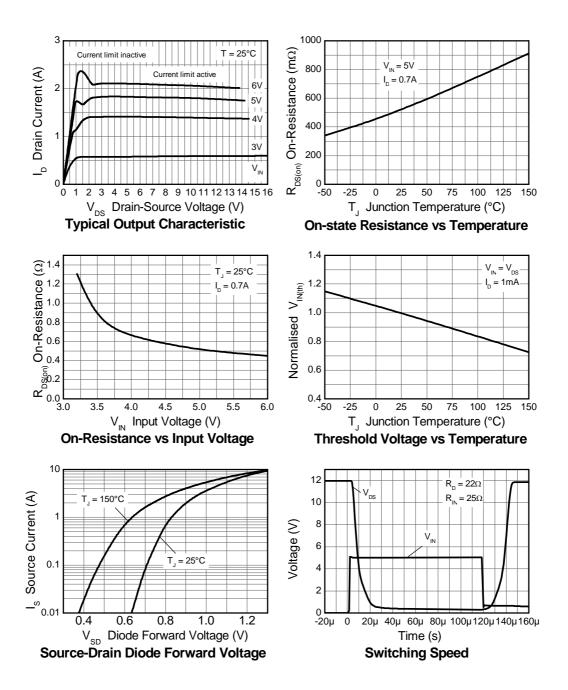


### Large copper area characteristics

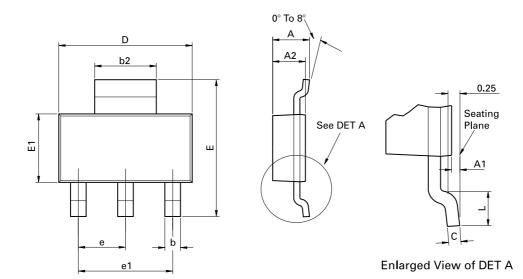
For large copper area as described in note (a)

Max Ambient Temperature T <sub>A</sub>	Maximum continuous current V <sub>IN</sub> =5V
25°C at Vin=5V	1140
70°C at Vin=5V	915
85°C at Vin=5V	825
125°C at Vin=5V	510





## Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millin	Millimeters		Inches		Millin	neters	Inc	hes
Dini.	Min.	Max.	Min.	Max.	Dim.	Min.	Max.	Min.	Max.
А	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	е	2.30	BSC	0.090	5 BSC
A2	1.55	1.65	0.0610	0.0649	e1	4.60	BSC	0.181	BSC
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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